

Features

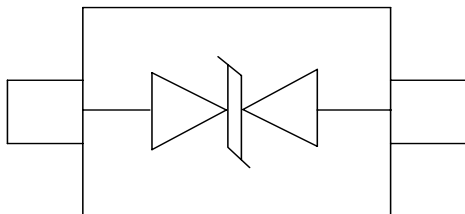
- Protects one data line
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test Air discharge: $\pm 25\text{kV}$
 - Contact discharge: $\pm 22\text{kV}$
- IEC61000-4-5 (Lightning) 2.5A (8/20 μs)
- RoHS Compliant

**Mechanical Characteristics**

- Package: SOD-523
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Dimensions and Pin Configuration

Circuit and Pin Schematic

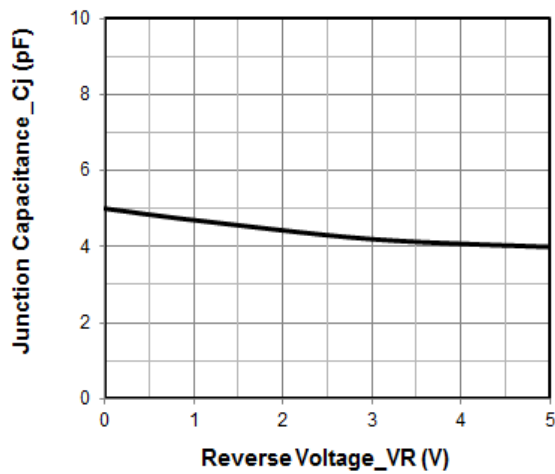
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	30	W
Peak Pulse Current (8/20 μs)	Ipp	2.5	A
ESD per IEC 61000-4-2 (Air)	VESD	± 25	kV
ESD per IEC 61000-4-2 (Contact)		± 22	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

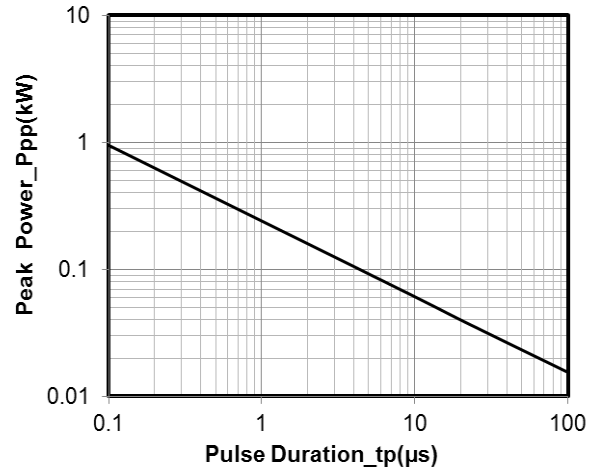
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6		8	V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 5V
Clamping Voltage	VC		8.5	9	V	Ipp = 1A (8 x 20 μs pulse)
Clamping Voltage	VC		10	12	V	Ipp = 2.5A (8 x 20 μs pulse)
Junction Capacitance	CJ		5		pF	VR = 0V, f = 1MHz

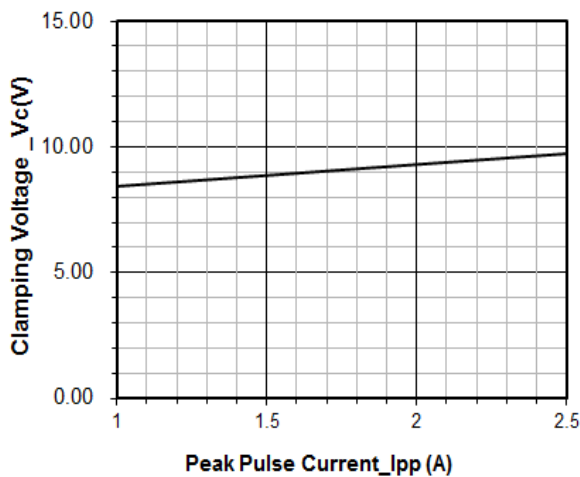
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



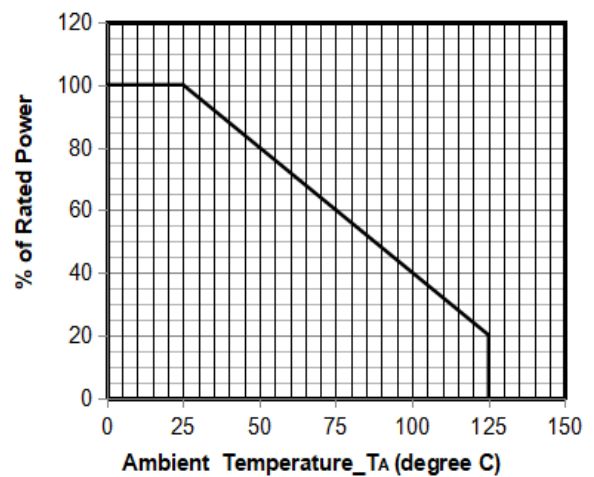
Junction Capacitance vs. Reverse Voltage



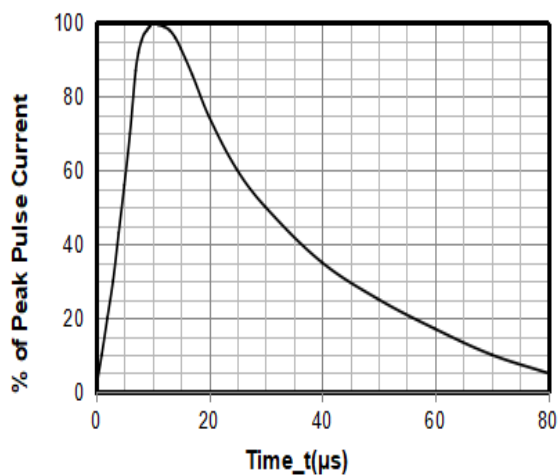
Peak Pulse Power vs. Pulse Time



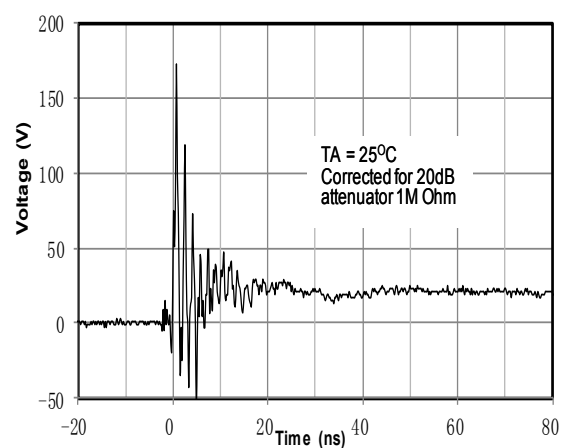
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20 μs Pulse Waveform

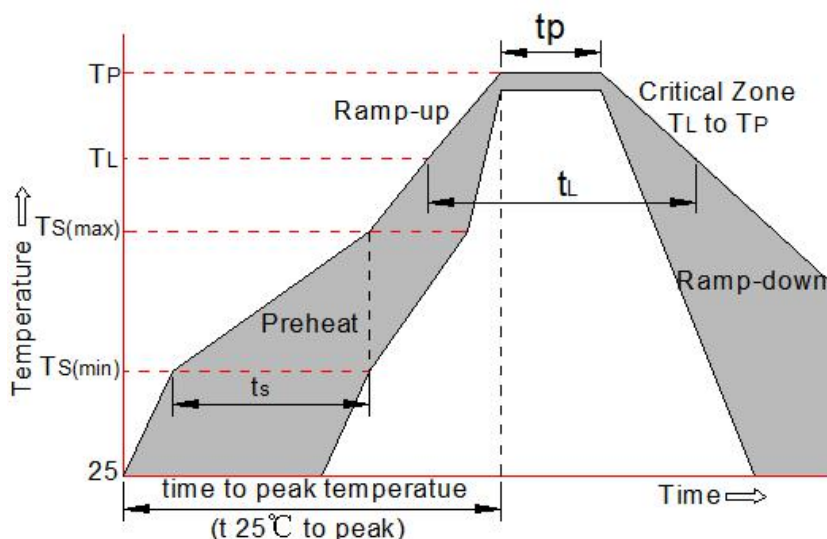


ESD Clamping Voltage

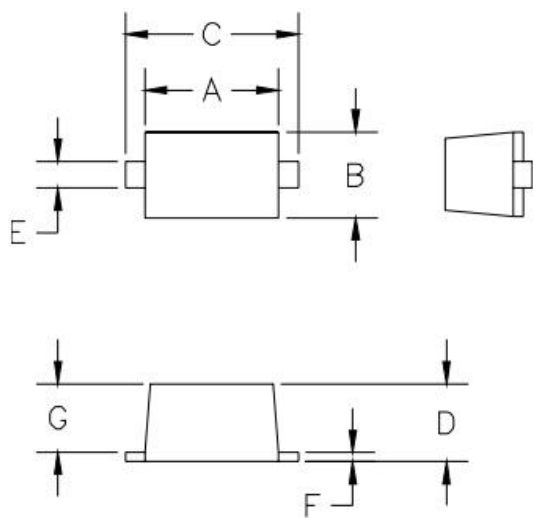
8 kV Contact per IEC61000-4-2

Soldering parameters

Reflow Condition		Pb-Free assembly (see FIG.2)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C



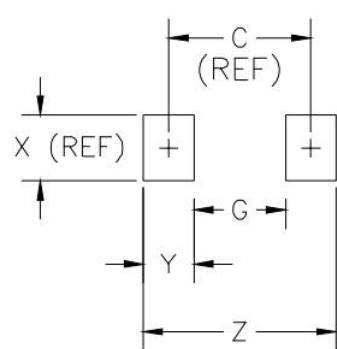
Package mechanical data



DIMENSIONS					
DIM ^N	INCHES		MM [1]		NOTE
	MIN	MAX	MIN	MAX	
A	.043	.051	1.10	1.30	—
B	.028	.035	0.70	0.90	—
C	.059	.067	1.50	1.70	—
D	.020	.028	0.50	0.70	—
E	.010	.014	0.25	0.35	—
F	.004	.008	0.10	0.20	—
G	.020	.028	0.50	0.70	—

[1] CONTROLLING DIMENSION: MILLIMETERS

Suggested Land Pattern



DIMENSIONS					
DIM ^N	INCHES		MM [1]		NOTE
	MIN	MAX	MIN	MAX	
C	—	.067	—	1.70	REF
G	—	.043	—	1.10	—
X	—	.031	—	0.80	REF
Y	—	.024	—	0.60	—
Z	—	.091	—	2.30	—

[1] CONTROLLING DIMENSION: MILLIMETERS

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